

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|----------------------------------|---------------------------------------------|------------------|---------|------------------|
| L1 | 2 | "thermal model" near gap | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:43 |
| L2 | 424471 | resist | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:43 |
| L3 | 19876 | diffusion and amplification | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:43 |
| L4 | 27 | "diffusion amplification" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L5 | 2 | 1 and 2 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L6 | 10 | 2 and 4 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L7 | 2 | 1 and 4 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L8 | 1176 | hotplate and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L9 | 578 | L8 and thermal and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L10 | 62 | L9 and zones | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:44 |
| L11 | 6 | L10 and 3 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:46 |
| L12 | 4 | 700/121 and "thermal model" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:47 |

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|-----|------|----------------------------------|---------------------------------------------|----|----|------------------|
| L13 | 3374 | warping and gap and thermal | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:48 |
| L14 | 2039 | 13 and stress\$3 | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:48 |
| L15 | 771 | 14 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:48 |
| L16 | 172 | 15 and "critical dimension" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:48 |
| L17 | 171 | 16 and plate | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:49 |
| L18 | 7 | 17 not inkjet | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:50 |
| L19 | 2 | "diffusion-amplification model" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:50 |
| L20 | 2 | "diffusion amplification model" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:50 |
| L21 | 27 | "diffusion amplification" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:50 |
| S1 | 1176 | hotplate and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 11:17 |
| S2 | 578 | S1 and thermal and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 11:17 |
| S3 | 62 | S2 and zones | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 12:54 |

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| S4 | 3 | "6127288" | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | ON | 2006/01/20 16:33 |
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